2PB1424

20 V, 3 A PNP low V_{CEsat} (BISS) transistor Rev. 02 — 15 January 2007

Product data sheet

Product profile

1.1 General description

PNP low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a medium power SOT89 (SC-62/TO-243) flat lead Surface-Mounted Device (SMD) plastic package.

NPN complement: 2PD2150.

1.2 Features

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- High efficiency due to less heat generation
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors

1.3 Applications

- DC-to-DC conversion
- MOSFET gate driving
- Motor control
- Charging circuits
- Power switches (e.g. motors, fans)
- Thin Film Transistor (TFT) backlight inverter

1.4 Quick reference data

Table 1. **Quick reference data**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	-20	V
I_{C}	collector current		-	-	-3	Α
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	-	– 5	Α
V _{CEsat}	collector-emitter saturation voltage	$I_C = -2 A;$ $I_B = -0.1 A$	<u>[1]</u> -	-0.2	-0.5	V

^[1] Pulse test: $t_p \le 300 \ \mu s; \ \delta \le 0.02.$



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2. Pinning information

Table 2. Pinning

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Pin	Description	Simplified outline	Symbol	
1	emitter		2	
2	collector		3 — 1	
3	base	3 2 1		
			006aaa231	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
2PB1424	SC-62	plastic surface-mounted package; collector pad for good heat transfer; 3 leads	SOT89

4. Marking

Table 4. Marking codes

Type number	Marking code
2PB1424	M1

5. Limiting values

Table 5. Limiting values

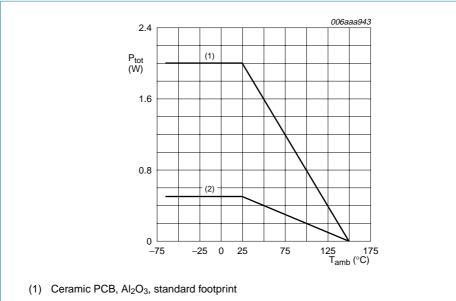
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	-20	V
V_{CEO}	collector-emitter voltage	open base	-	-20	V
V_{EBO}	emitter-base voltage	open collector	-	-6	V
I _C	collector current		-	-3	Α
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	- 5	Α
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	<u>[1]</u> _	0.5	W
			[2] _	2	W
Tj	junction temperature		-	150	°C
T_{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[2] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

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(2) FR4 PCB, standard footprint

Fig 1. Power derating curves

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	3 ,	in free air	<u>[1]</u> -	-	250	K/W
junction t	junction to ambient		[2] _	-	62	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

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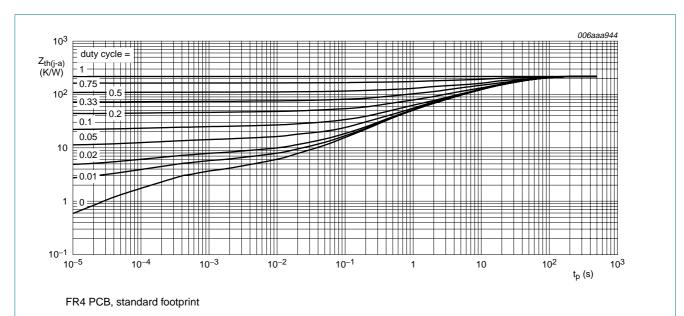


Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

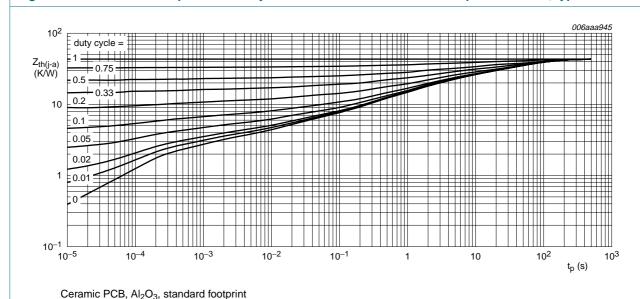


Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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7. Characteristics

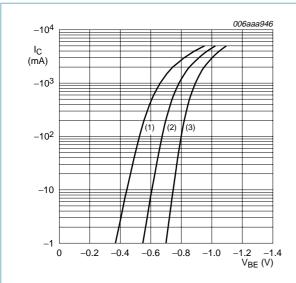
Table 7. Characteristics

 $T_{amb} = 25 \,^{\circ}C$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I_{CBO}	collector-base cut-off current	$V_{CB} = -20 \text{ V}; I_E = 0 \text{ A}$	-	-	-0.1	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}$	-	-	-0.1	μΑ
h _{FE}	DC current gain	$V_{CE} = -2 \text{ V}; I_{C} = -0.1 \text{ A}$	180	-	390	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -2 A$; $I_B = -0.1 A$	<u>[1]</u> _	-0.2	-0.5	V
f _T	transition frequency	$V_{CE} = -2 \text{ V; } I_E = 0.5 \text{ A;}$ f = 100 MHz	-	125	-	MHz
C_{ib}	common-base input capacitance	$V_{EB} = -5 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	130	-	pF
C_ob	common-base output capacitance	$V_{CB} = -10 \text{ V}; I_E = i_e = 0 \text{ A};$ $f = 1 \text{ MHz}$	-	37	-	pF

^[1] Pulse test: $t_p \le 300 \ \mu s; \ \delta \le 0.02.$

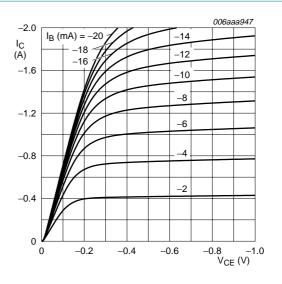
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 $V_{CE} = -2 V$

- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -40 \, ^{\circ}C$

Fig 4. Collector current as a function of base-emitter voltage; typical values



T_{amb} = 25 °C

Fig 5. Collector current as a function of collector-emitter voltage; typical values

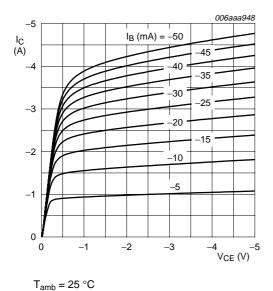
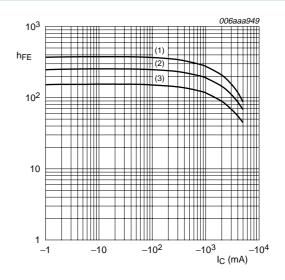


Fig 6. Collector current as a function of collector-emitter voltage; typical values

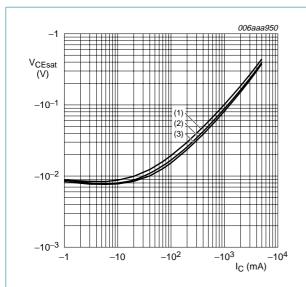


 $V_{CE} = -2 V$

- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -40 \, ^{\circ}C$

Fig 7. DC current gain as a function of collector current; typical values

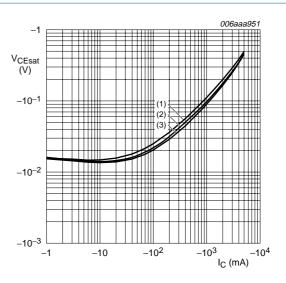
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$$I_{\rm C}/I_{\rm B} = 10$$

- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -40 \, ^{\circ}C$

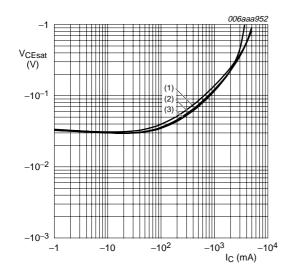
Fig 8. Collector-emitter saturation voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -40 \, ^{\circ}C$

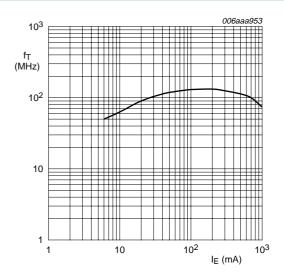
Fig 9. Collector-emitter saturation voltage as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B} = 50$

- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -40 \, ^{\circ}C$

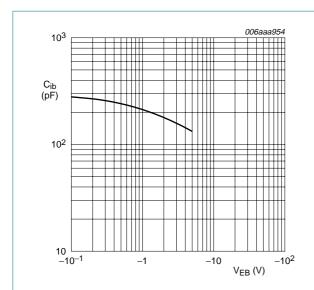
Fig 10. Collector-emitter saturation voltage as a function of collector current; typical values



 $T_{amb} = 25 \, ^{\circ}C; \, V_{CE} = -2 \, V$

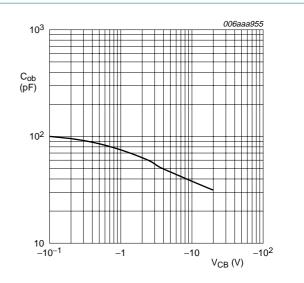
Fig 11. Transition frequency as a function of emitter current; typical values

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 T_{amb} = 25 °C; f = 1 MHz; I_E = i_e = 0 A

Fig 12. Common-base input capacitance as a function of emitter-base voltage; typical values

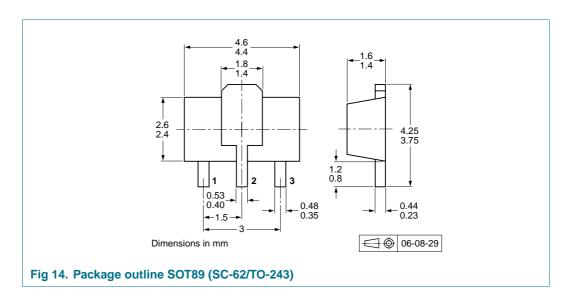


 T_{amb} = 25 °C; f = 1 MHz; I_E = i_e = 0 A

Fig 13. Common-base output capacitance as a function of collector-base voltage; typical values

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8. Package outline

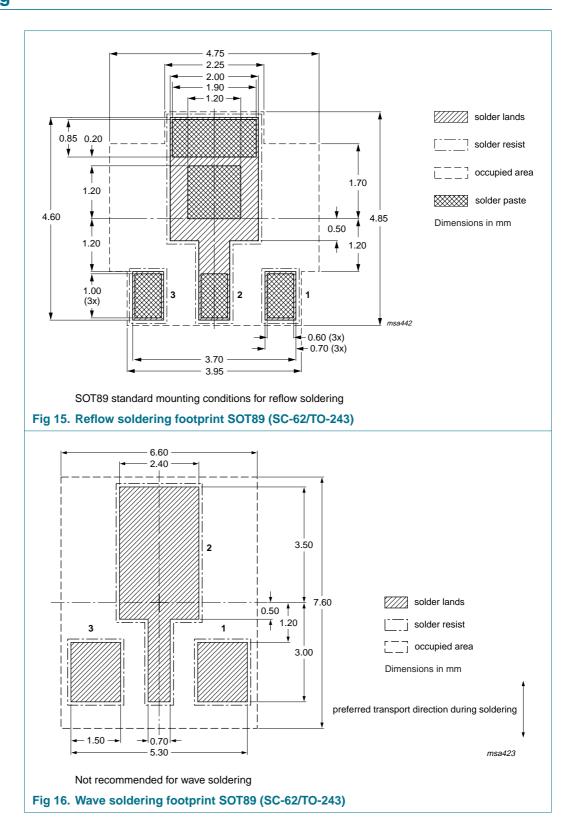


9. Packing information

Please refer to packing information on www.nexperia.com.

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10. Soldering



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11. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
2PB1424_2	20070115	Product data sheet	-	2PB1424_1		
Modifications:	 The format of t Semiconductor 	his data sheet has been redesi 's	gned to comply with the nev	v identity guidelines of NXP		
	 Legal texts have been adapted to the new company name where appropriate. 					
	• Table 1 "Quick	reference data": I _C collector cu	rrent added			
	• Table 1 "Quick	reference data": I _{CM} peak colle	ctor current maximum value	e adapted		
	• Table 1 "Quick	reference data": V _{CEsat} collecto	or-emitter saturation voltage	added		
	 Table 5 "Limiting 	ng values": V _{CBO} collector-base	voltage maximum value ad	apted		
	 Table 5 "Limiting 	 <u>Table 5 "Limiting values"</u>: V_{EBO} emitter-base voltage maximum value adapted 				
	 Table 5 "Limiting 	ng values": I _C collector current r	maximum value adapted			
	 Table 5 "Limiting 	ng values": I _{CM} peak collector c	urrent maximum value adap	ted		
	 <u>Table 5 "Limiting values"</u>: P_{tot} total power dissipation for ceramic PCB condition added 					
	• Figure 1 "Power derating curves": adapted					
	<u>Table 6 "Thermal characteristics"</u> : adapted					
	 <u>Table 6 "Thermal characteristics"</u>: R_{th(j-a)} thermal resistance from junction to ambient for ceramic PC condition added 					
	 Figure 2: t_p pulse time redefined to pulse duration 					
	• Figure 3: adde	d				
	 Table 7 "Chara 	cteristics": I _{CBO} collector-base	cut-off current conditions ad	apted		
	 Table 7 "Chara 	cteristics": V _{CEsat} collector-emi	tter saturation voltage typica	l value added		
	Table 7 "Chara	ue adapted				
	 <u>Table 7 "Characteristics"</u>: C_{ib} common-base input capacitance added <u>Table 7 "Characteristics"</u>: C_{ob} common-base output capacitance added 					
	• Figure 4, 6, 10, 11, 12, 13 and 16: added					
	• <u>Figure 5</u> , <u>7</u> , <u>8</u> a	and 9: adapted				
	 Section 12 "Leg 	gal information": updated				
2PB1424_1	20050502	Product data sheet	-	-		

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12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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Date

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